



#### **60V P-CHANNEL ENHANCEMENT MODE MOSFET**

### **Product Summary**

BV <sub>DSS</sub>	R <sub>DS(on)</sub>	I <sub>D</sub> T <sub>A</sub> = +25°C
-60V	125mΩ @ V <sub>GS</sub> = -10V	-4.3A
-00 V	190mΩ @ V <sub>GS</sub> = -4.5V	-3.5A

#### **Features and Benefits**

- · Fast Switching Speed
- Low Gate Drive
- Low Input Capacitance
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

#### **Description**

This MOSFET is designed to minimize the on-state resistance yet maintain superior switching performance, which makes it ideal for high-efficiency power management applications.

### **Applications**

- Motor Control
- DC-DC Converters
- Power Management Functions
- Uninterrupted Power Supply

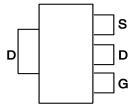
#### **Mechanical Data**

- Case: SOT223
- Case Material: Molded Plastic, UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish—Matte Tin Annealed over Copper Leadframe.
  Solderable per MIL-STD-202, Method 208
- Weight: 0.112 grams (Approximate)

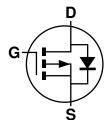
SOT223



Top View



Pin Out—Top View



Equivalent Circuit

#### Ordering Information (Notes 4 & 5)

Part Number	Compliance	Case	Packaging
ZXMP6A17GQTA	Automotive	SOT223	1000/Tape & Reel
ZXMP6A17GQTC	Automotive	SOT223	4000/Tape & Reel

Notes:

- 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to https://www.diodes.com/quality/.
- 5. For packaging details, see http://www.diodes.com/products/packages.html.

### **Marking Information**

ZXMP & 6A17 &

ZXMP6A17 = Product Type Marking Code YWW = Date Code Marking Y or Y = Year (ex: 8 = 2018) WW or WW = Week (01 - 53)



# **Maximum Ratings** (@ $T_A = +25^{\circ}C$ , unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Drain-Source Voltage		$V_{DSS}$	-60	V	
Gate-Source Voltage		$V_{GS}$	±20	V	
		(Note 7)		-4.3	
Continuous Drain Current	$V_{GS} = 10V$	$T_A = +70^{\circ}C \text{ (Note 7)}$	l <sub>D</sub>	-3.5	Α
		(Note 6)		-3	
Pulsed Drain Current	V <sub>GS</sub> = 10V	(Note 8)	I <sub>DM</sub>	-13.7	Α
Continuous Source Current (	(Body Diode)	(Note 7)	I <sub>S</sub>	-4.8	Α
Pulsed Source Current (Body Diode) (Note 8)		I <sub>SM</sub>	-13.7	Α	

#### Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

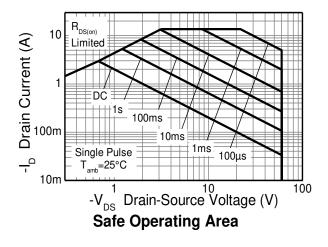
Characteristic		Symbol	Value	Unit	
Power Dissipation	(Note 6)	9	2 16		
Linear Derating Factor	(Note 7)	P <sub>D</sub>	3.9 31	mW/°C	
Thermal Resistance, Junction to Ambient	(Note 6)	Б	62.5		
	(Note 7)	R <sub>OJA</sub>	32	°C/W	
Thermal Resistance, Junction to Lead	(Note 9)	Rejl	9.8		
Operating and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C	

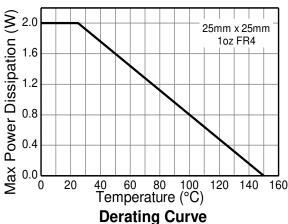
Notes:

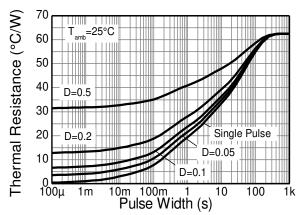
- 6. For a device surface mounted on 25mm × 25mm × 1.6mm FR4 PCB with high coverage of single-sided 1oz copper. In still air conditions; the device is measured when operating in a steady-state condition.
- 7. Same as Note 6 except the device is measured at  $t \leq 10 s. \label{eq:total_sample}$
- 8. Same as Note 6 except the device is pulsed with D = 0.02 and pulse width of 300µs. The pulse current is limited by the maximum junction temperature.
- 9. Thermal resistance from junction to solder point (at the end of the drain lead).

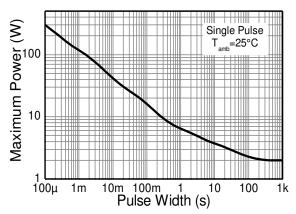


## **Thermal Characteristics**









**Transient Thermal Impedance** 

**Pulse Power Dissipation** 



## Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

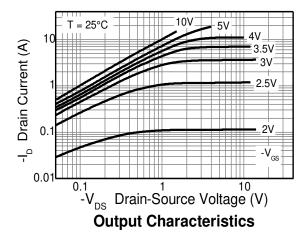
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-60	_	_	V	$I_D = -250 \mu A, V_{GS} = 0 V$	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	_	_	-0.5	μΑ	$V_{DS} = -60V, V_{GS} = 0V$	
Gate-Source Leakage	I <sub>GSS</sub>	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS							
Gate Threshold Voltage	$V_{GS(th)}$	-1	_	_	V	$I_D = -250 \mu A, V_{DS} = V_{GS}$	
Static Dunin Course On Benintanna (Note 10)	_		0.096	0.125	0	V <sub>GS</sub> = -10V, I <sub>D</sub> = -2.2A	
Static Drain-Source On-Resistance (Note 10)	R <sub>DS(ON)</sub>	_	0.12	0.19	Ω	V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -1.8A	
Forward Transconductance (Notes 10 & 11)	g <sub>fs</sub>	_	4.7	_	S	V <sub>DS</sub> = -15V, I <sub>D</sub> = -2.2A	
Diode Forward Voltage (Note 10)	V <sub>SD</sub>	_	-0.85	-0.95	V	I <sub>S</sub> = -2A, V <sub>GS</sub> = 0V, T <sub>J</sub> = +25°C	
Reverse Recovery Time (Note 11)	t <sub>rr</sub>		25.1	_	ns	$I_S = -1.7A$ , di/dt = 100A/ $\mu$ s,	
Reverse Recovery Charge (Note 11)	Q <sub>rr</sub>	_	27.2	_	nC	T <sub>J</sub> = +25°C	
DYNAMIC CHARACTERISTICS (Note 11)							
Input Capacitance	Ciss	_	637	_	pF	.,	
Output Capacitance	Coss	_	70	_	pF	V <sub>DS</sub> = -30V, V <sub>GS</sub> = 0V - f = 1MHz	
Reverse Transfer Capacitance	C <sub>rss</sub>	_	53	_	pF		
Total Gate Charge (Note 12)	Qg	_	9	_	nC	V <sub>GS</sub> = -4.5V	
Total Gate Charge (Note 12)	Qg	_	17.7	_	nC	V <sub>DS</sub> = -30V	
Gate-Source Charge (Note 12)	Q <sub>gs</sub>	_	1.6	_	nC	$V_{GS} = -10V$ $I_{D} = -2.2A$	
Gate-Drain Charge (Note 12)	$Q_{gd}$	_	4.4	_	nC	1	
Turn-On Delay Time (Note 12)	t <sub>D(on)</sub>	_	2.6	_	ns		
Turn-On Rise Time (Note 12)	t <sub>r</sub>	_	3.4	_	ns	$V_{DD}$ = -30V, $V_{GS}$ = -10V $I_D$ = -1A, $R_G \cong 6\Omega$	
Turn-Off Delay Time (Note 12)	t <sub>D(off)</sub>	_	26.2	_	ns		
Turn-Off Fall Time (Note 12)	t <sub>f</sub>	_	11.3		ns		

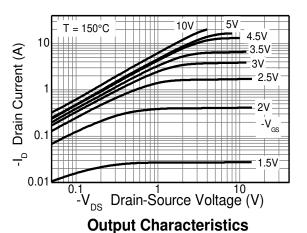
Notes:

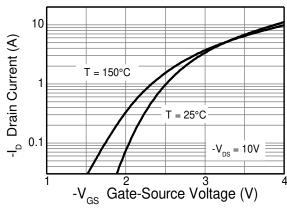
<sup>10.</sup> Measured under pulsed conditions. Pulse width  $\le$  300µs; duty cycle  $\le$  2%. 11. For design aid only—not subject to production testing. 12. Switching characteristics are independent of operating junction temperatures.

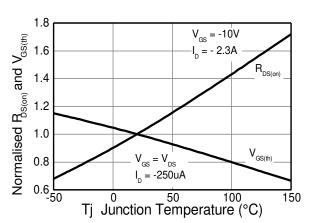


## **Typical Characteristics**



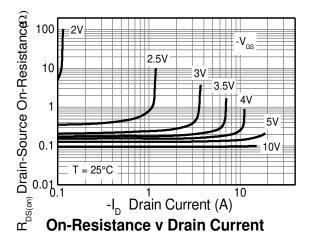


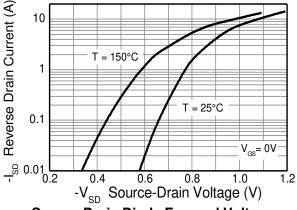




**Typical Transfer Characteristics** 



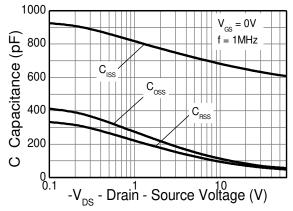




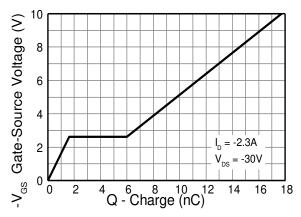
**Source-Drain Diode Forward Voltage** 



## Typical Characteristics (continued)

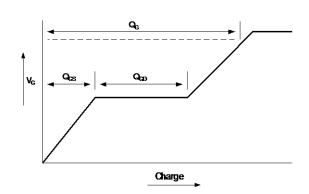


**Capacitance v Drain-Source Voltage** 

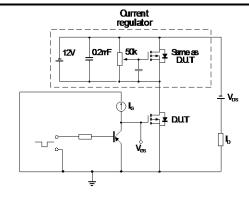


Gate-Source Voltage v Gate Charge

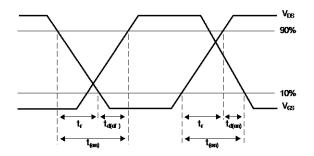
## **Test Circuits**



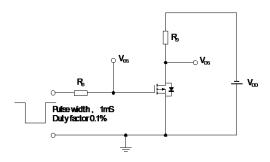
Basic gate charge waveform



Gate charge test circuit



Switching time waveforms

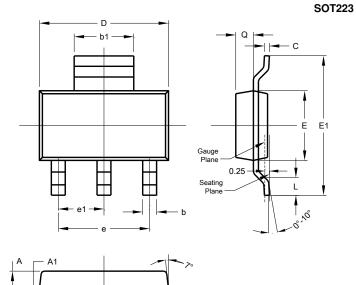


Switching time test circuit



## **Package Outline Dimensions**

 $Please \ see \ http://www.diodes.com/package-outlines.html \ for \ the \ latest \ version.$ 

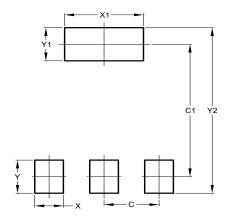


SOT223					
Dim	Min	Max	Тур		
Α	1.55	1.65	1.60		
A1	0.010	0.15	0.05		
b	0.60	0.80	0.70		
b1	2.90	3.10	3.00		
С	0.20	0.30	0.25		
D	6.45	6.55	6.50		
Е	3.45	3.55	3.50		
E1	6.90	7.10	7.00		
е	-	-	4.60		
e1	-	-	2.30		
L	0.85	1.05	0.95		
Q	0.84	0.94	0.89		
All Dimensions in mm					

## **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### **SOT223**



Dimensions	Value (in mm)
С	2.30
C1	6.40
Х	1.20
X1	3.30
Υ	1.60
Y1	1.60
Y2	8.00



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